IN THE CLAIMS:

Please amend the claims as follows:

- 1. (Currently Amended) An apparatus for vaporizing a solid precursor, comprising:
- a housing having an interior volume and an inlet for receiving a carrier gas, wherein the interior volume is configured to receive a solid chemical precursor; and
- at least two surfaces contained in the housing <u>and having the solid chemical</u> <u>precursor applied thereto</u>, wherein each of the at least two surfaces comprise a heating element and are spaced to allow flow of the carrier gas therebetween.
- 2. (Original) The apparatus of claim 1, wherein the apparatus further comprises an outlet operably connected to a reaction chamber of a deposition chamber.
- 3. (Previously presented) The apparatus of claim 2, wherein the at least two surfaces are selected from the group consisting of a baffle, a rod, a mesh, and a grating.
- 4. (Previously presented) The apparatus of claim 1, wherein the at least two surfaces have a form selected from the group consisting of an s-shape, a linear shape and a cone shape.
- 5. (Currently Amended) The apparatus of claim 3, wherein the at least two surfaces comprise stainless steel and or ceramic.
- 6. (Previously presented) The apparatus of claim 2, wherein the deposition chamber is selected from the group consisting of an atomic layer deposition chamber, a chemical vapor deposition chamber, and an evaporative coating chamber.
- 7. (Original) The apparatus of claim 6, wherein the solid precursor includes a tantalum-containing precursor or a tungsten-containing precursor.

8. (Currently Amended) An apparatus for vaporizing a solid precursor, comprising:

a housing having an interior volume, wherein the interior volume is configured to receive a solid chemical precursor;

an inlet for receiving a carrier gas;

an outlet for delivering the carrier gas and a vaporized solid precursor, the vaporized solid precursor originating from the solid chemical precursor;

a first wall to support the inlet;

at least two surfaces contained in the housing and spaced to allow passage of the carrier gas, the at least two surfaces having the solid precursor applied thereto; and

a heating member contained in each of the at least two surfaces.

- 9. (Original) The apparatus of claim 8, wherein the outlet is operably connected to a reaction chamber of a deposition chamber.
- 10. (Previously presented) The apparatus of claim 9, wherein the at least two surfaces are selected from the group consisting of a baffle, a rod, a mesh, and a grating.

11. (Cancelled)

- 12. (Previously presented) The apparatus of claim 9, wherein the at least two surfaces have a form selected from the group consisting of an s-shape, a linear shape and a cone shape.
- 13. (Previously presented) The apparatus of claim 12, wherein the at least two surfaces comprise stainless steel or ceramic.

- 14. (Previously presented) The apparatus of claim 9, wherein the deposition chamber is selected from the group consisting of an atomic layer deposition chamber, a chemical vapor deposition chamber, and an evaporative coating chamber.
- 15. (Original) The apparatus of claim 14, wherein the solid precursor includes a tantalum-containing precursor or a tungsten-containing precursor.
- 16. (Currently Amended) An apparatus for vaporizing a solid tantalum-containing precursor, comprising:

a housing comprising an interior volume <u>having</u> an inlet for receiving a carrier gas and an outlet for delivering the carrier gas and a vaporized solid precursor, wherein the vaporized solid precursor originates from the solid tantalum-containing precursor;

at least two surfaces contained in the housing <u>and having the solid tantalum-containing precursor applied thereto</u>, wherein the at least two surfaces are configured to heat the solid tantalum-containing precursor and are spaced to allow passage of the carrier gas therebetween; and

at least one heating member contained in at least one wall of the housing wherein the outlet is operably connected to a reaction chamber of a deposition chamber.

- 17. (Previously presented) The apparatus of claim 16, wherein the at least two surfaces are independently selected from the group consisting of a baffle, a rod, a mesh and a grating.
- 18. (Cancelled)
- 19. (Previously presented) The apparatus of claim 16, wherein the deposition chamber is selected from the group consisting of an atomic layer deposition chamber, a chemical vapor deposition chamber, and an evaporative coating chamber.
- 20. (Cancelled)

21. (Currently Amended) An apparatus for vaporizing a solid tantalum-containing precursor, comprising:

a housing having an interior volume configured to receive the solid tantalumcontaining precursor;

an inlet for receiving a carrier gas;

at least two baffles in thermal communication with the solid tantalum-containing precursor, the at least two baffles <u>having the solid tantalum-containing precursor</u> <u>applied thereto and spaced to allow passage of the carrier gas;</u>

an outlet for delivering the carrier gas and a vapor originating from the solid tantalum-containing precursor, the outlet operably connected to an atomic layer deposition chamber; and

a heating member contained in each of the at least two baffles.